



Exar Quarterly Quality and Reliability Report

August 2010

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Outgoing Quality (PPM) Data

The outgoing quality data are the results of electrical and visual/mechanical inspection on samples of all Exar's products. The results are measured in parts per million (PPM).

Quarterly QC Visual PPM Report

Quarter: April 1, 2010 to June 30, 2010

Devices: Exar Products

Summary: All data is first submission data

Total number of lots inspected:	2468
Total number of lots accepted:	2467
Total number of QC samples inspected:	373,465
Total number fail in QC samples:	1

Process average PPM: $= \Sigma r / \Sigma n \times 10^6$ $= 1 / 373,465 \times 10^6$ r = Total number fail in QC samples n = Total number of QC samples inspected	2.6 PPM
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Quarterly QC Electrical PPM Report

Quarter: April 1, 2010 to June 30 , 2010

Devices: Exar Products

Summary: All data is first submission data

Total number of lots inspected:	5209
Total number of lots accepted:	5209
Total number of QC samples inspected:	1,527,822
Total number fail in QC samples:	0

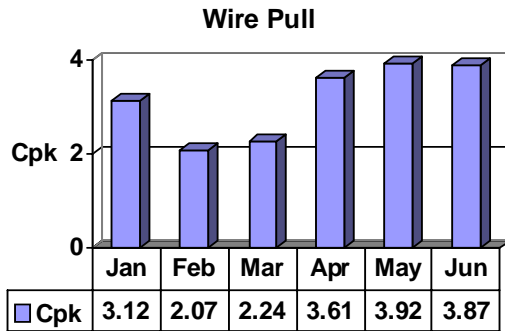
Process average PPM: $= \Sigma r / \Sigma n \times 10^6$ $= 0 / 1,527,822 \times 10^6$ r = Total number fail in QC samples n = Total number of QC samples inspected	0 PPM
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SPC – Cpk Trends

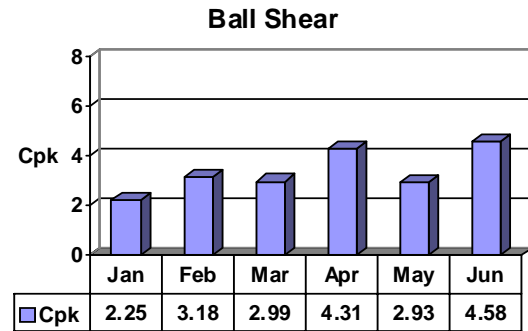
Data on Cpk and Cpk trends for critical processes of Exar's assembly subcontractors and foundry fabs are reported in order to assure our customers that our suppliers have an on-going SPC plan to control and continually improve their critical processes. This also serves as an early warning system which keeps processes from becoming marginal.

Unisem, Indonesia SPC Program: 2009 / 2010

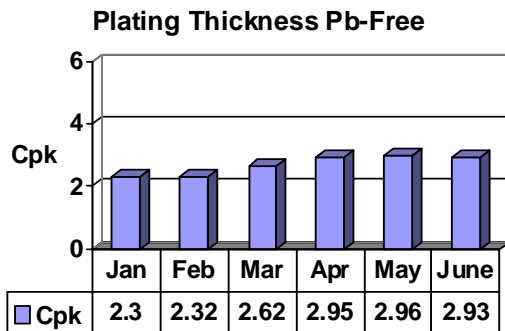
Package Technology: LQFP



LSL = 6 gms

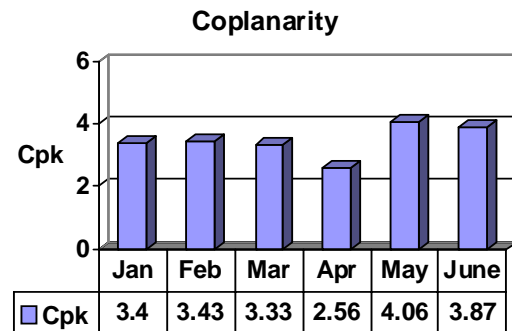


LSL = 20 gms



LSL = 300µin

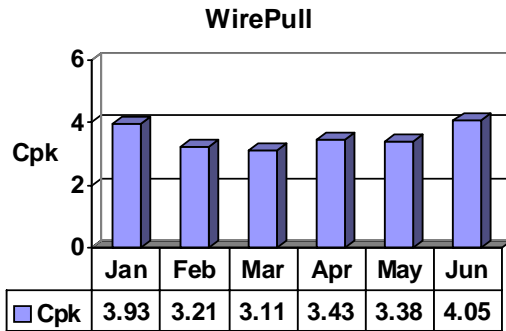
USL = 800µin



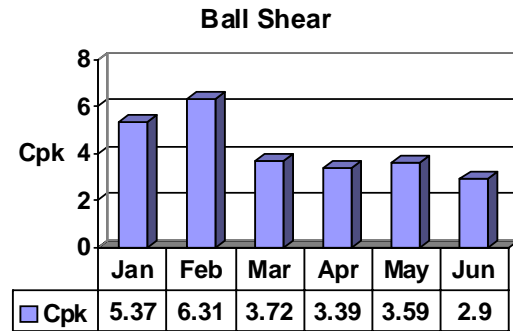
USL = 2.0 mils

Unisem, Indonesia SPC Program: 2009 / 2010

Package Technology: PDIP



LSL = 6 gms

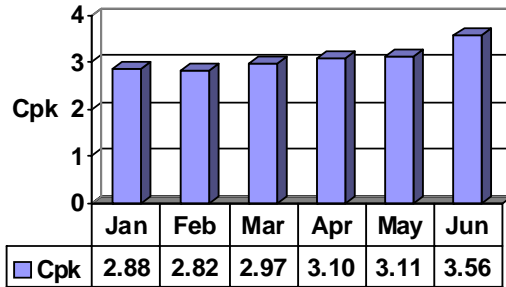


LSL = 20 gms

Unisem, Indonesia SPC Program: 2009 / 2010

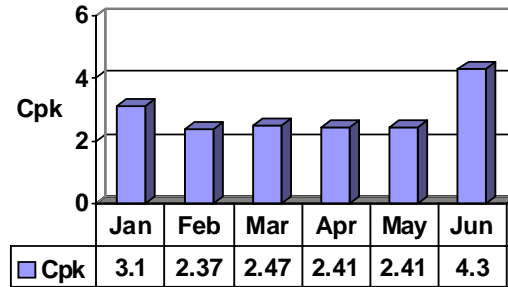
Package Technology: PLCC

Wire Pull



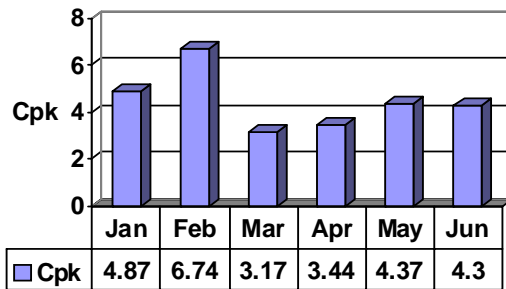
LSL = 6 gms

Ball Shear



LSL = 20 gms

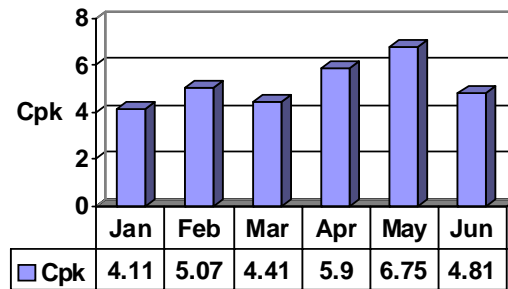
Plating Thickness Pb-Free



LSL = 300µin

USL = 800µin

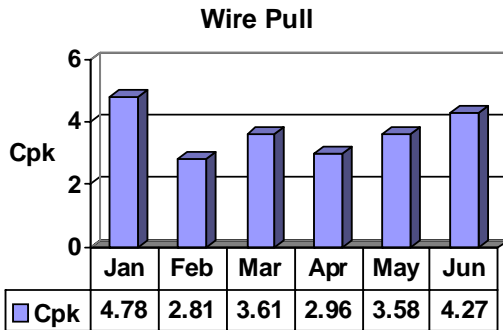
Coplanarity



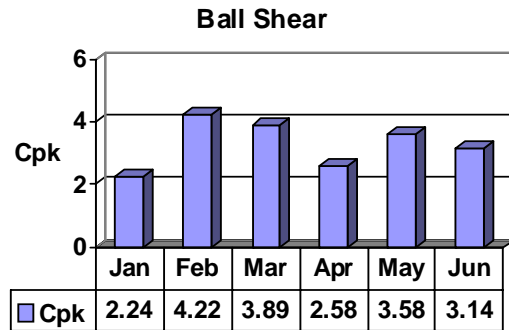
USL = 3.0 mils

Unisem, Indonesia SPC Program: 2009 / 2010

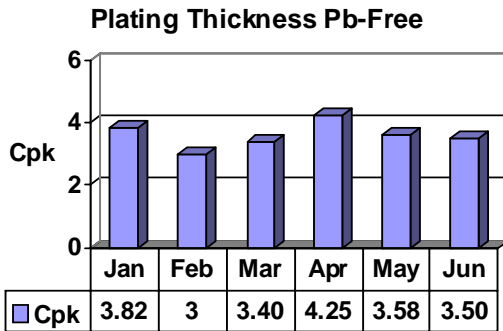
Package Technology: SOIC



LSL = 6 gms



LSL = 20 gms

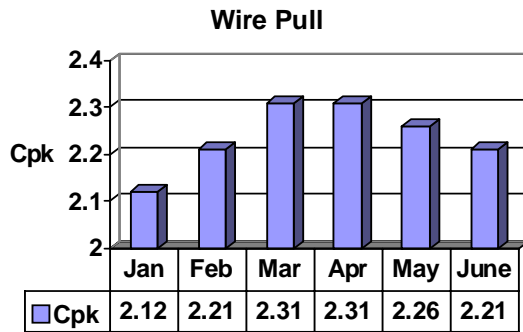


LSL = 300µin

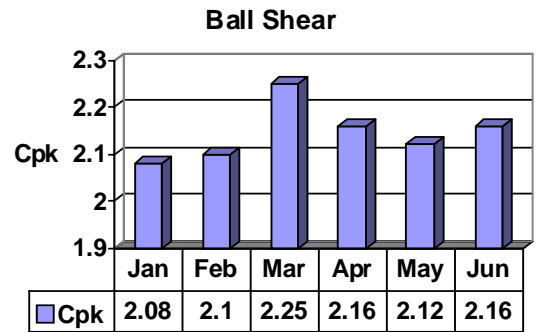
USL = 800µin

Unisem, Ipoh SPC Program: 2009 / 2010

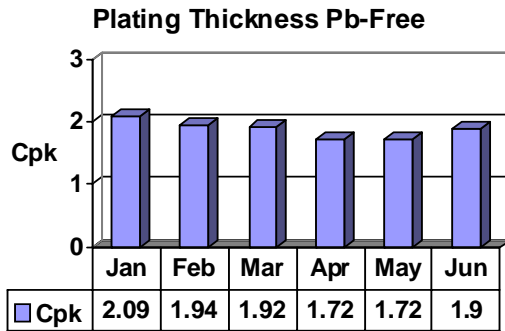
Package Technology: NSOIC



LSL = 6 gms



LSL = 20 gms

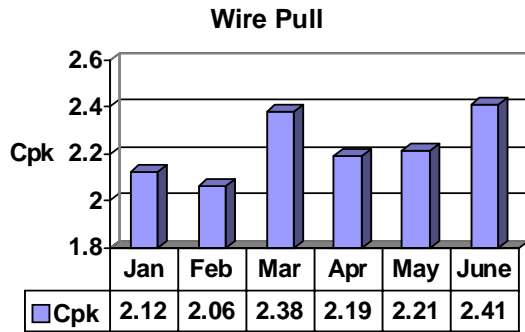


LSL = 300µin

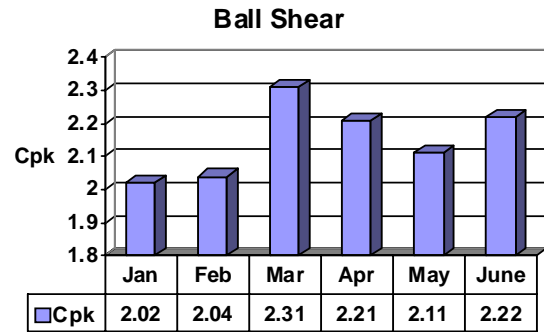
USL = 800µin

Unisem, Ipoh SPC Program: 2009 / 2010

Package Technology: PDIP



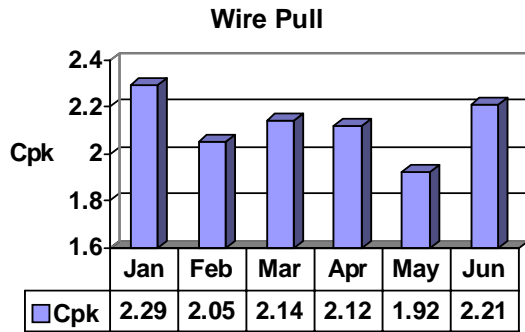
LSL = 6 gms



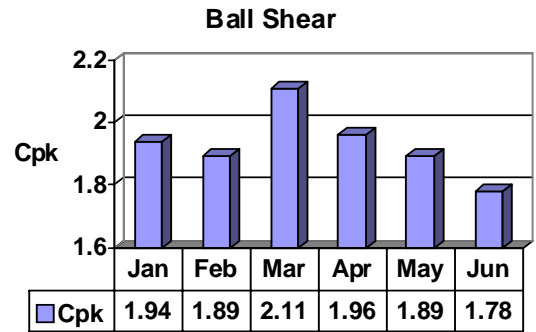
LSL = 20 gms

Unisem, Ipoh SPC Program: 2009 / 2010

Package Technology: SOT223



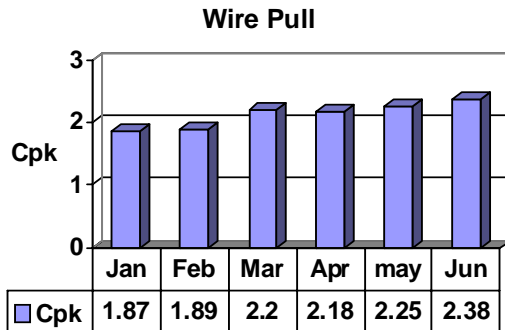
LSL = 6 gms



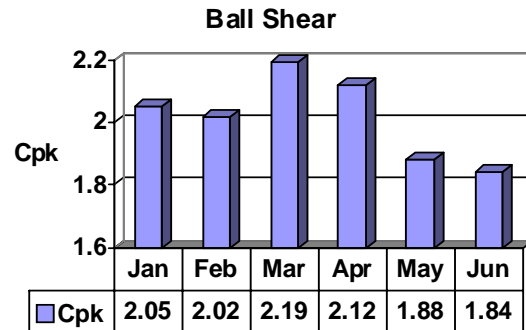
LSL = 20 gms

Unisem, Ipoh SPC Program: 2009 / 2010

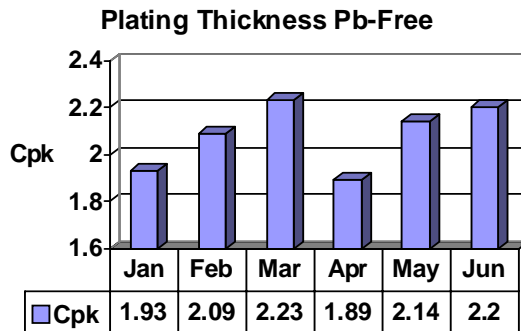
Package Technology: SOT23



LSL = 6 gms



LSL = 20 gms

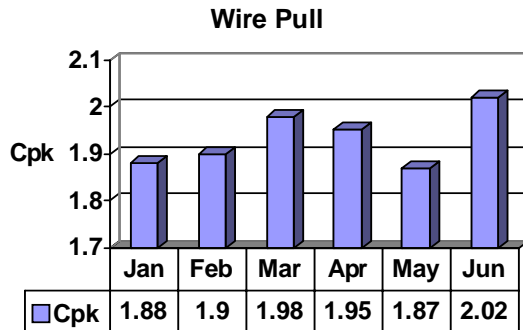


LSL = 300µin

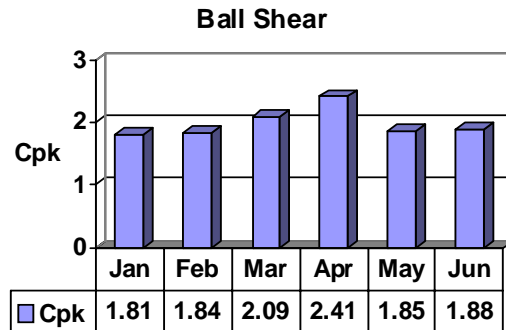
USL = 800µin

Unisem, Ipoh SPC Program: 2009 / 2010

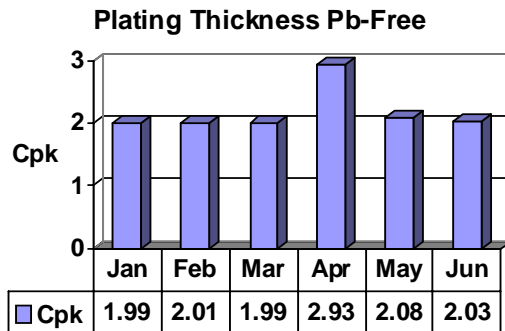
Package Technology: MSOP



LSL = 6 gms



LSL = 20 gms

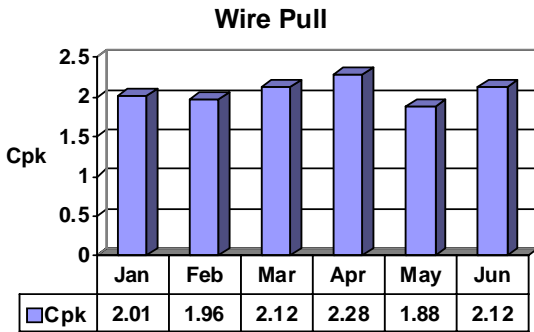


LSL = 300µin

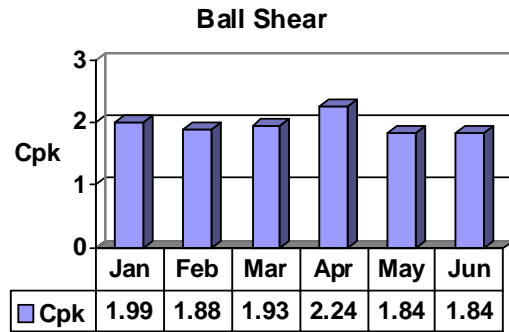
USL = 800µin

Unisem, Ipoh SPC Program: 2009 / 2010

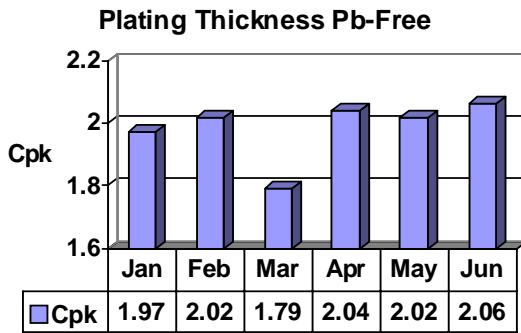
Package Technology: TSSOP



LSL = 6 gms



LSL = 20 gms

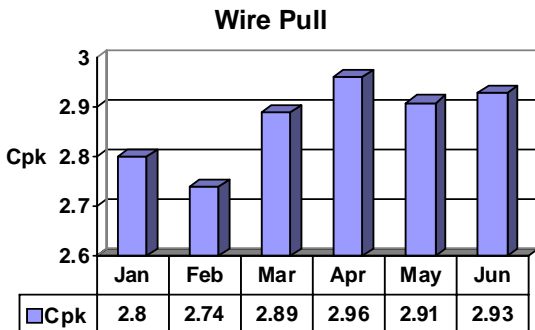


LSL = 300µin

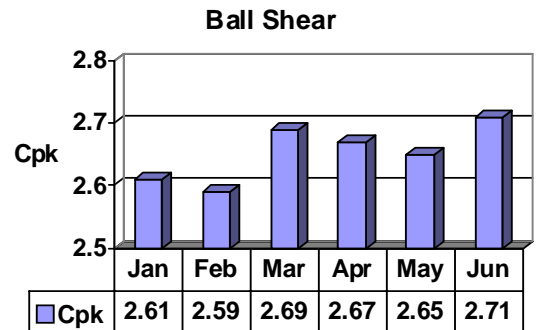
USL = 800µin

Carsem M, Malaysia Program: 2009 / 2010

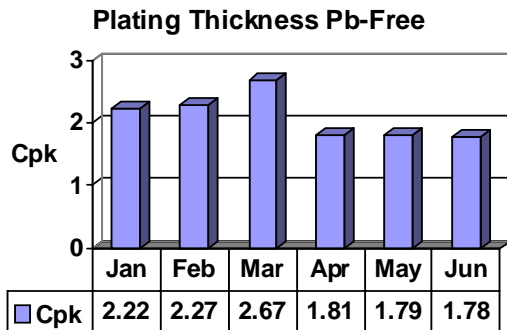
Package Technology: MSOP



LSL = 6 gms

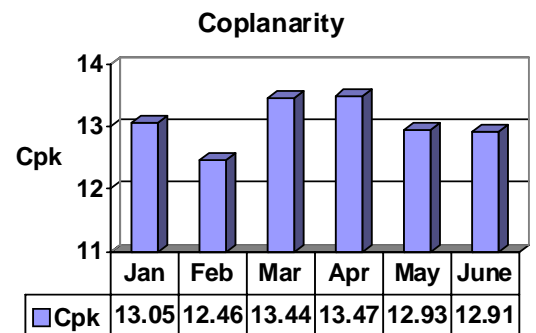


LSL = 20 gms



LSL = 300µin

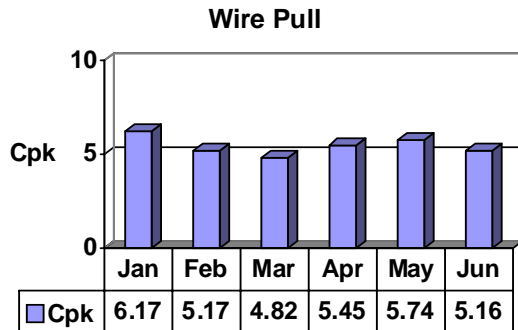
USL = 800µin



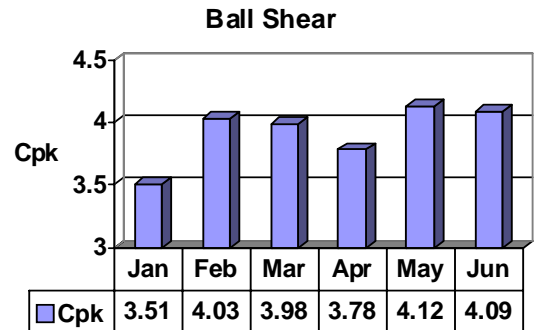
USL = 3.0 mils

Carsem M, Malaysia Program: 2009 / 2010

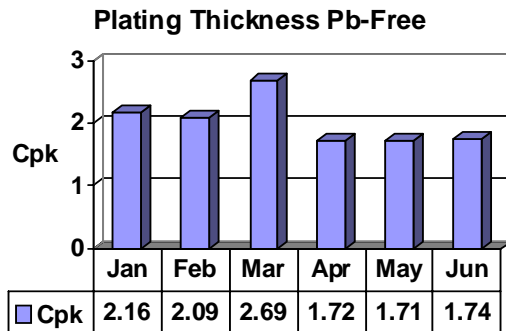
Package Technology: TO220



LSL = 6 gms



LSL = 20 gms

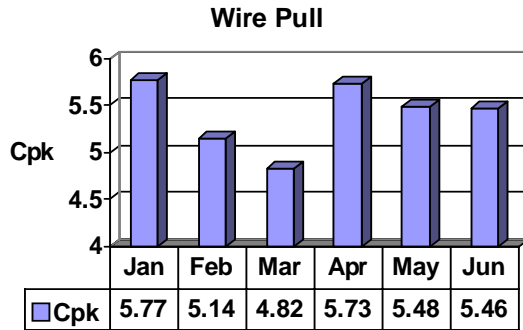


LSL = 300µin

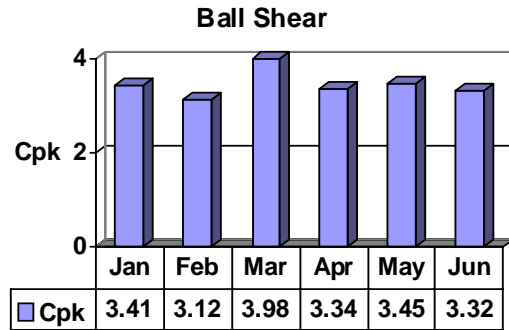
USL = 800µin

Carsem M, Malaysia Program: 2009 / 2010

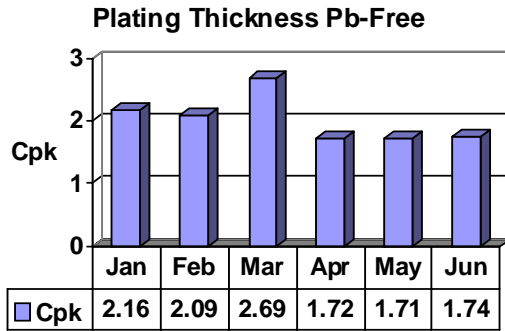
Package Technology: TO263



LSL = 6 gms

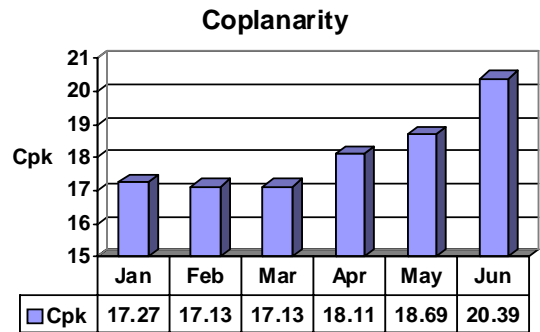


LSL = 20 gms



LSL = 300µin

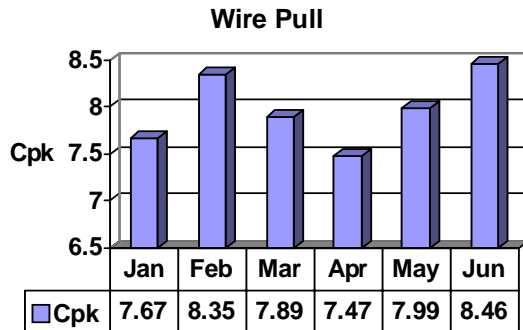
USL = 800µin



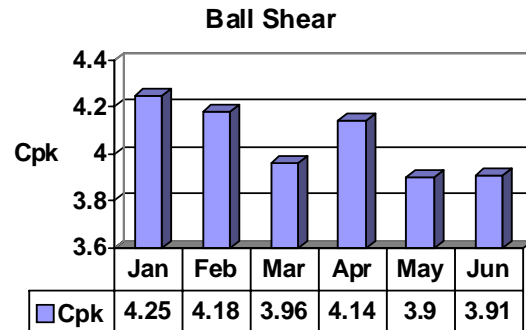
USL = 3.0 mils

Carsem M, Malaysia Program: 2009 / 2010

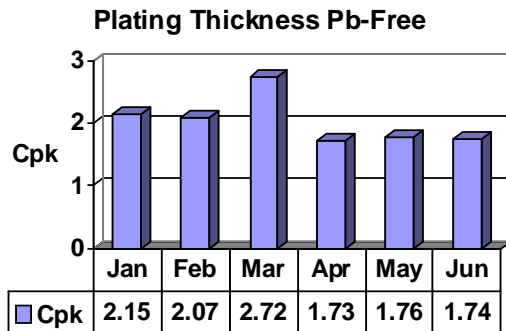
Package Technology: SOT223



LSL = 6 gms



LSL = 20 gms

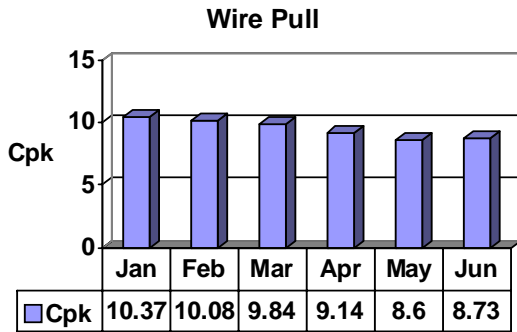


LSL = 300µin

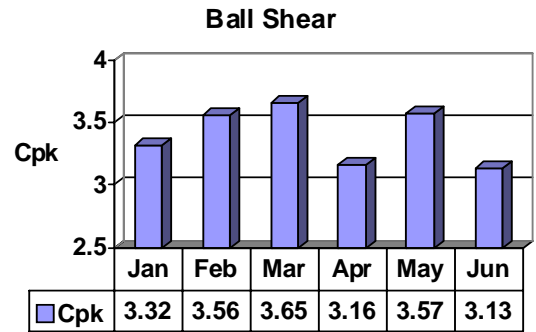
USL = 800µin

Carsem M, Malaysia Program: 2009 / 2010

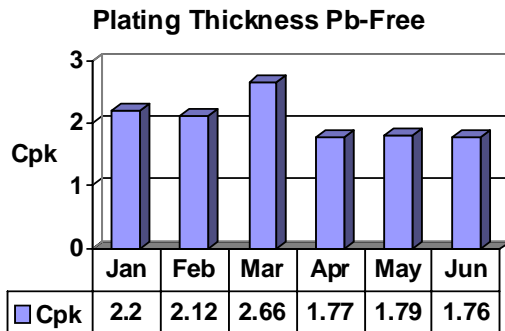
Package Technology: SC70



LSL = 6 gms



LSL = 20 gms

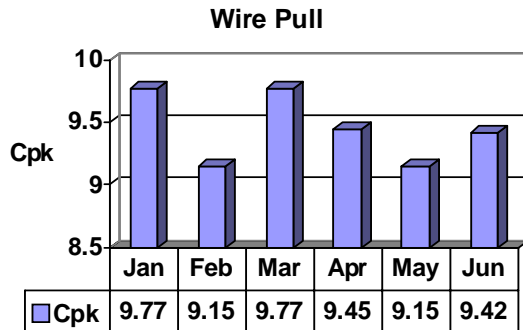


LSL = 300µin

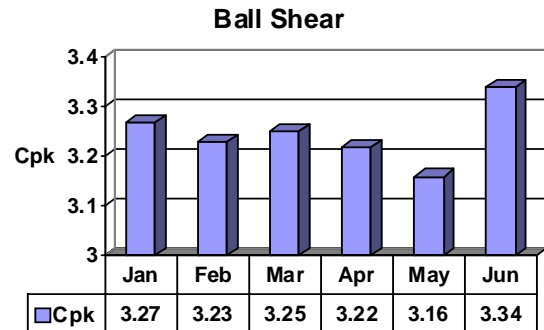
USL = 800µin

Carsem M, Malaysia Program: 2009 / 2010

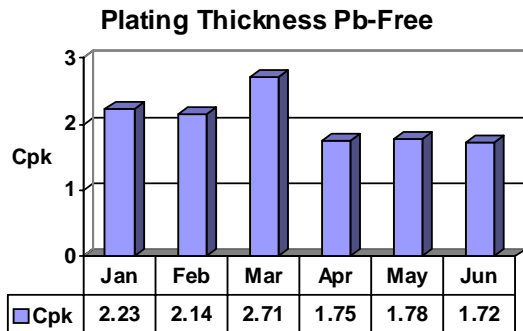
Package Technology: SOT23



LSL = 6 gms



LSL = 20 gms

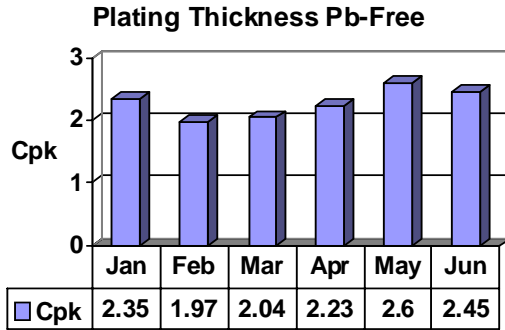


LSL = 300µin

USL = 800µin

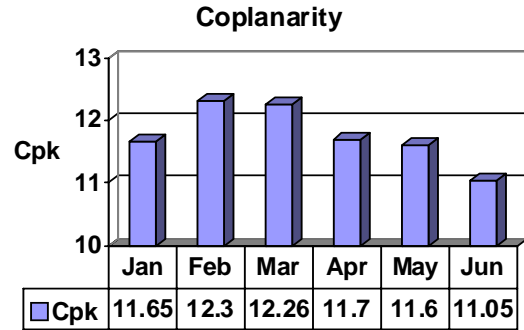
Carsem S, Malaysia Program: 2009 / 2010

Package Technology: TSSOP



LSL = 300 μ in

USL = 800 μ in

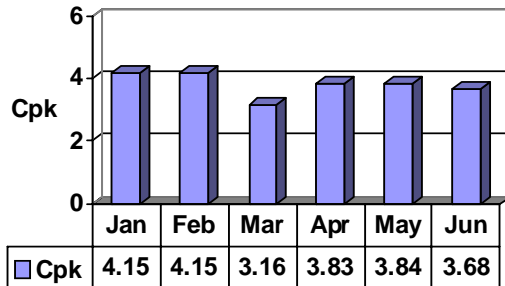


USL = 3.0 mils

Carsem S, Malaysia Program: 2009 / 2010

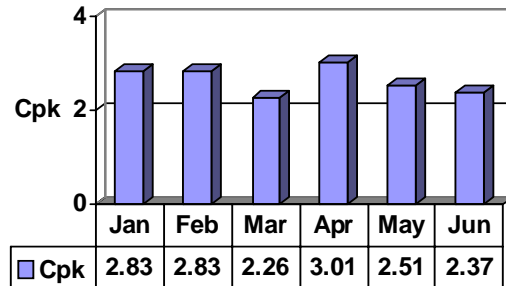
Package Technology: QFP

Wire Pull



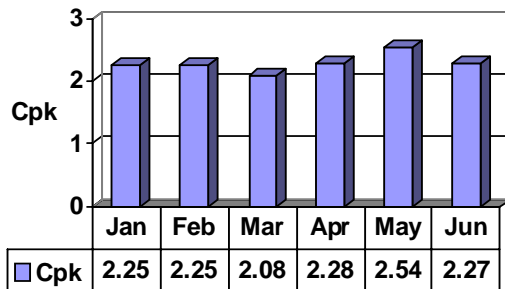
LSL = 6 gms

Ball Shear



LSL = 20 gms

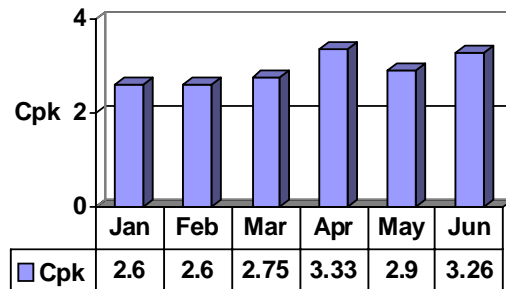
Plating Thickness Pb-Free



LSL = 300µin

USL = 800µin

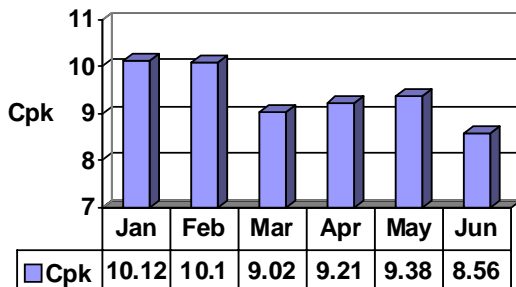
Plating Comp (%Sn)



LSL = 80%

USL = 90%

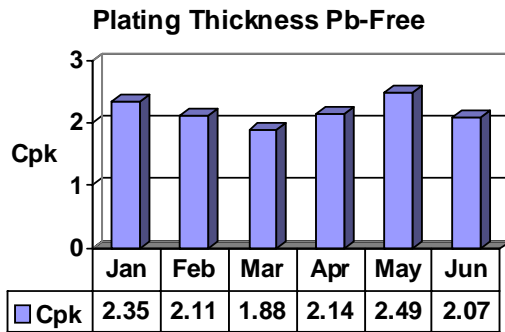
Coplanarity



USL = 3.0 mils

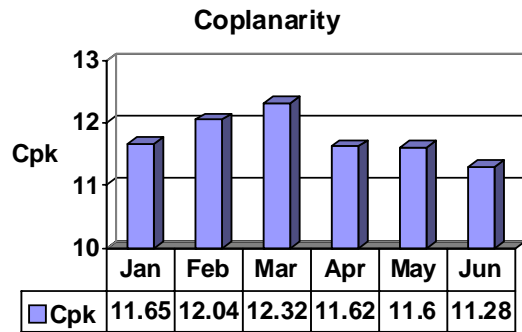
Carsem S, Malaysia Program: 2009 / 2010

Package Technology: SSOP



LSL = 300 μ in

USL = 800 μ in

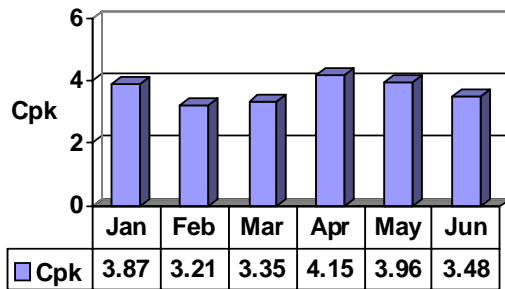


USL = 3.0 mils

Carsem S, Malaysia Program: 2009 / 2010

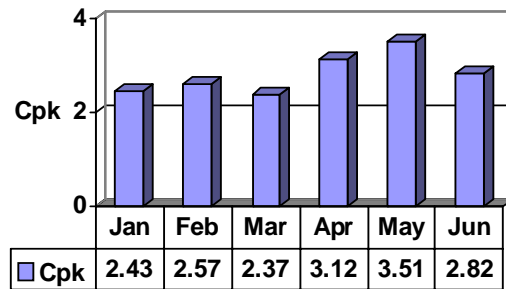
Package Technology: WSOIC

Wire Pull



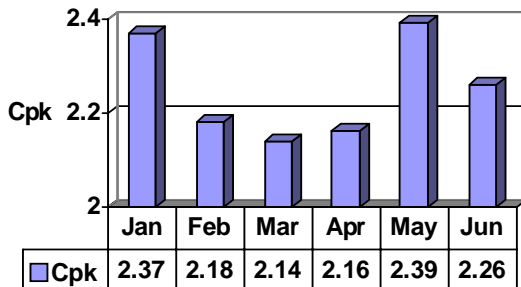
LSL = 6 gms

Ball Shear



LSL = 20 gms

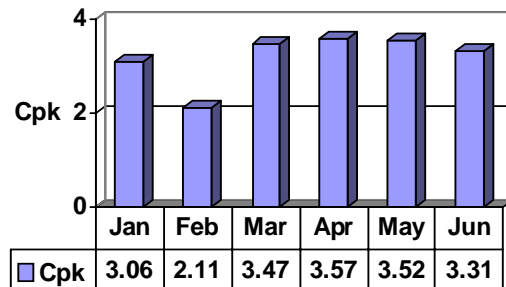
Plating Thickness Pb-Free



LSL = 300µin

USL = 800µin

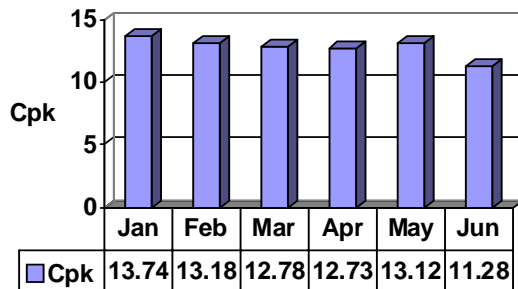
Plating Comp (%Sn)



LSL = 80%

USL = 90%

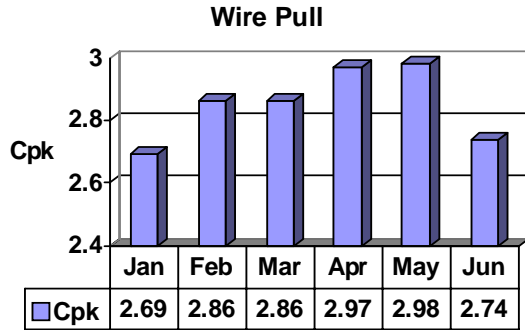
Coplanarity



USL = 3.0 mils

Carsem S, Malaysia Program: 2009 / 2010

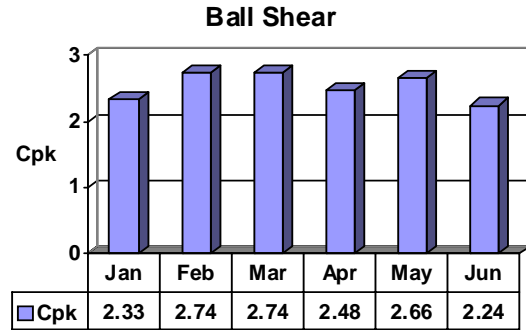
Package Technology: PDIP



LSL = 6 gms

LSL = 300 μ in

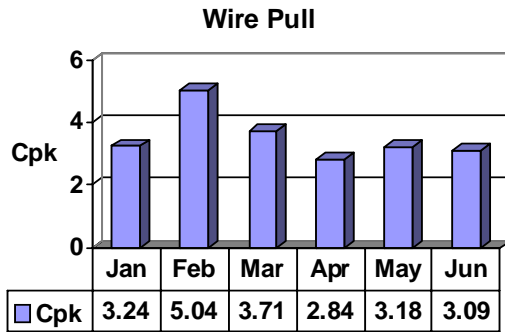
USL = 800 μ in



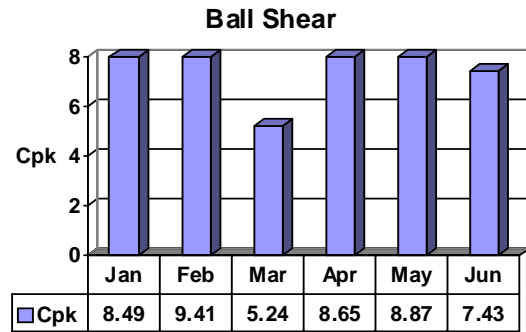
LSL = 20 gms

UTAC, China Program: 2009 / 2010

Package Technology: BGA



LSL = 3 gms

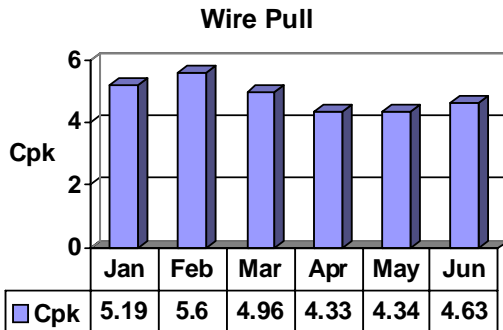


LSL = 8 grams

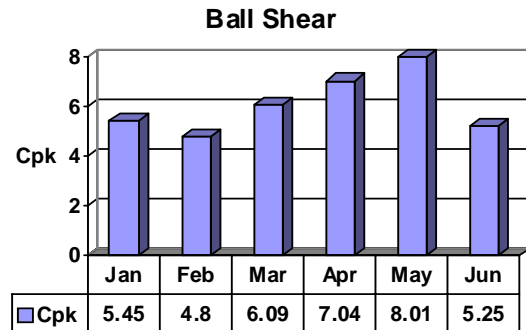
SPC – Cpk Trends - Assembly

UTAC, China Program: 2009 / 2010

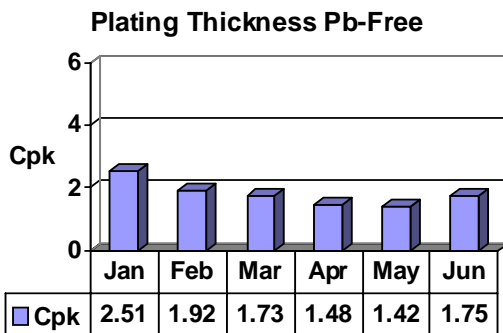
Package Technology: QFP



LSL = 3 gms

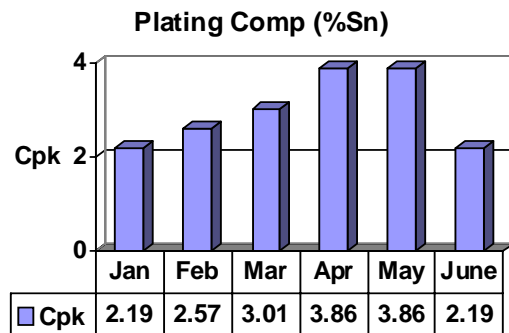


LSL = 20 gms



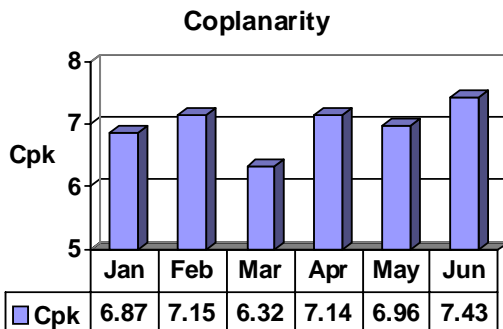
LSL = 300µin

USL = 800µin



LSL = 80%

USL = 90%

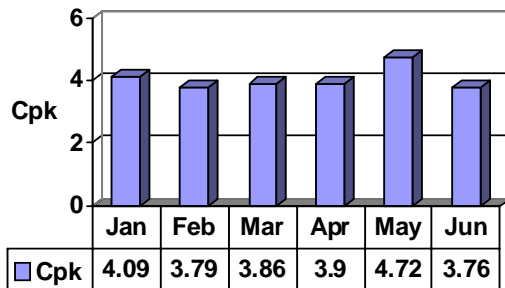


USL = 3.0 mils

UTAC, China Program: 2009 / 2010

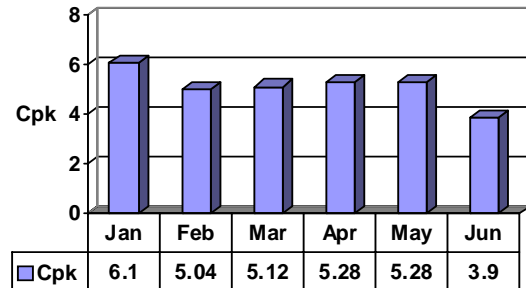
Package Technology: LPCC

Wire Pull



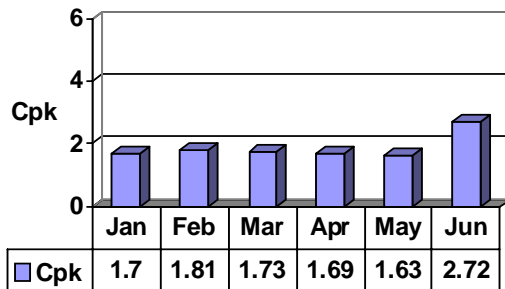
LSL = 6 gms

Ball Shear



LSL = 20 gms

Plating Thickness Pb-Free



LSL = 300µin

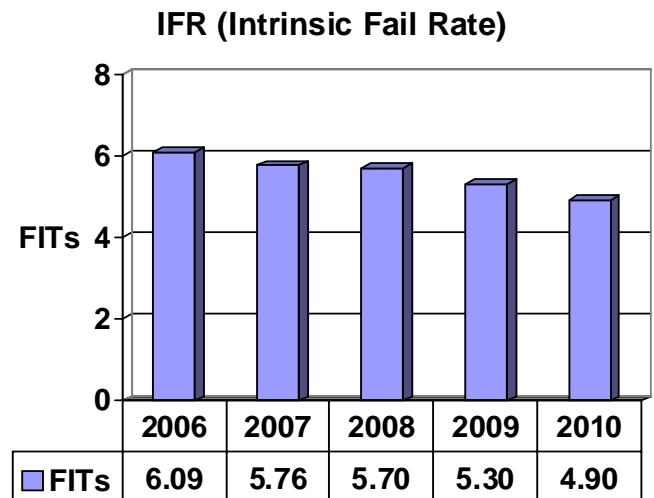
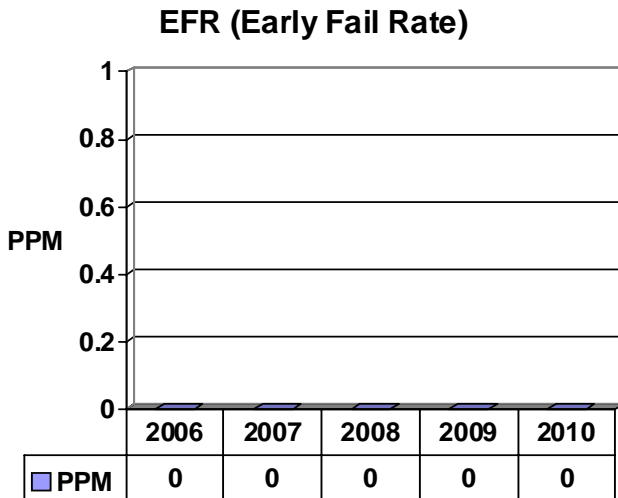
USL = 800µin

Reliability

Reliability data trends of Exar's wafer fab processes and package types are reported in order to assure our customers that our foundry fabs and assembly subcontractors are continuing to improve their reliability performance.

Factory: GLOBALFOUNDRIES, Singapore

Process: 0.25 μ /0.35 μ CMOS



Year	Sample Size	# Fail	PPM
2006	315	0	0
2007	90	0	0
2008	20	0	0
2009	105	0	0
2010	70	0	0

Year	Sample Size	Device Hours	# Fail
2006	270	208,080	0
2007	90	90,000	0
2008	20	20,000	0
2009	105	105,000	0
2010	70	75,000	0

FIT: Failure in Time; 60% CL, 55°C, Ea = .7eV

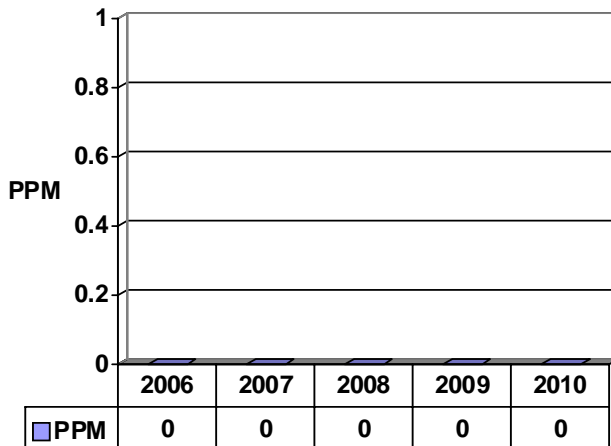
IFR: Intrinsic Failure Rate > 168 hours @ the test temperature of 125°C or > 72 hours @ 150°C

IFR: Early Failure Rate < 168 hours @ the test temperature of 125°C or < 72 hours @ 150°C

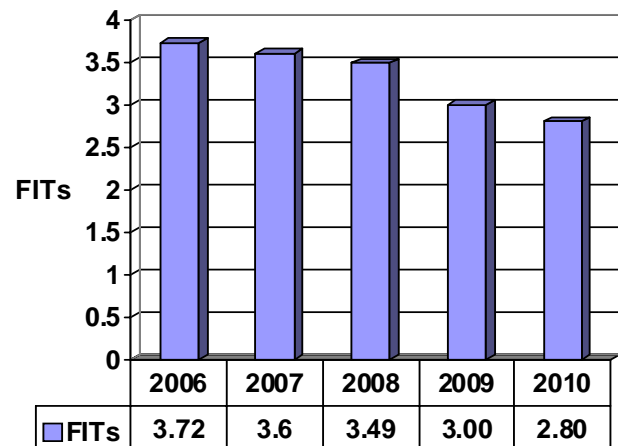
Factory: GLOBALFOUNDRIES Fab 2, Singapore

Process: 0.6 μ CMOS

EFR (Early Fail Rate)



IFR (Intrinsic Fail Rate)



Year	Sample Size	# Fail	PPM
2005	369	0	0
2006	498	0	0
2007	90	0	0
2008	100	0	0
2009	180	0	0
2010	90	0	0

Year	Sample Size	Device Hours	# Fail
2005	323	323,000	0
2006	498	498,000	0
2007	90	90,000	0
2008	100	100,000	0
2009	180	180,000	0
2010	90	90,000	0

FIT: Failure in Time; 60% CL, 55°C, Ea = .7eV

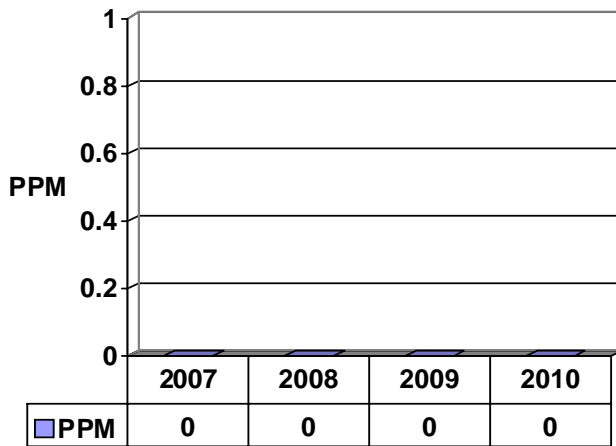
IFR: Intrinsic Failure Rate > 168 hours @ the test temperature of 125°C or > 72 hours @ 150°C

IFR: Early Failure Rate < 168 hours @ the test temperature of 125°C or < 72 hours @ 150°C

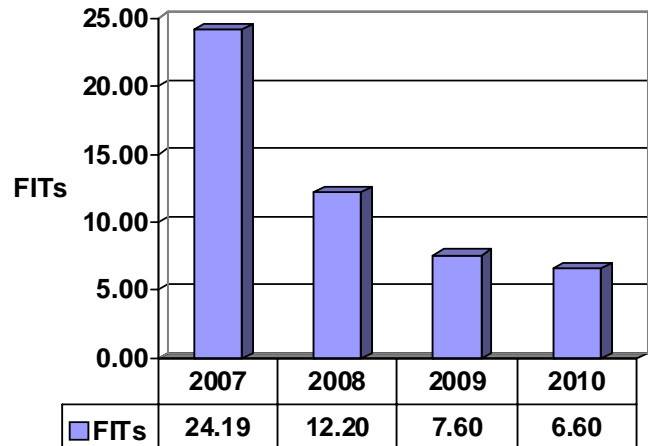
Factory: Tower/Jazz, USA

Process: 0.5 μ CMOS

EFR (Early Fail Rate)



IFR (Intrinsic Fail Rate)



Year	Sample Size	# Fail	PPM
2007	486	0	0
2008	311	0	0
2009	747	0	0
2010	229	0	0

Year	Sample Size	Device Hours	# Fail
2007	486	486,000	0
2008	311	311,000	0
2009	747	747,000	0
2010	229	229,000	0

FIT: Failure in Time; 60% CL, 55°C, Ea = .7eV

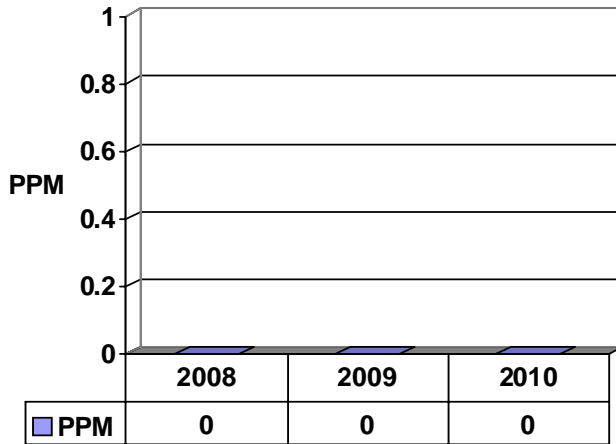
IFR: Intrinsic Failure Rate > 168 hours @ the test temperature of 125°C or > 72 hours @ 150°C

IFR: Early Failure Rate < 168 hours @ the test temperature of 125°C or < 72 hours @ 150°C

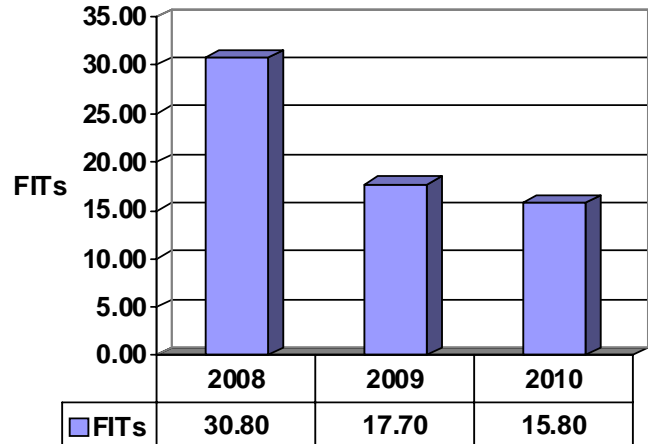
Factory: Polar, USA

Process: 0.5 μ BiCMOS

EFR (Early Fail Rate)



IFR (Intrinsic Fail Rate)



Year	Sample Size	# Fail	PPM
2008	267	0	0
2009	280	0	0
2010	80	80	0

Year	Sample Size	Device Hours	# Fail
2008	387	387,000	0
2009	280	280,000	0
2010	80	80,000	0

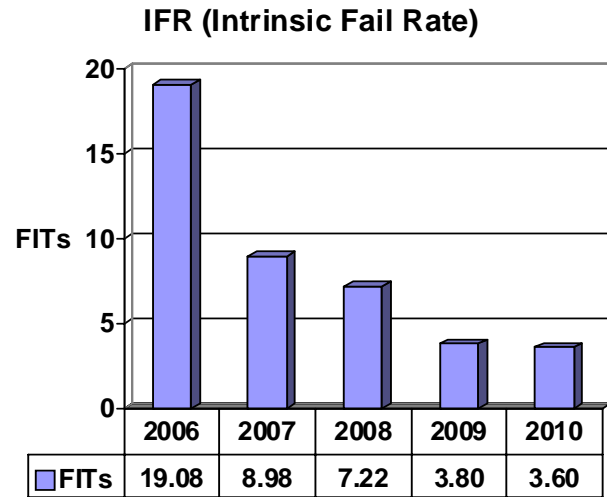
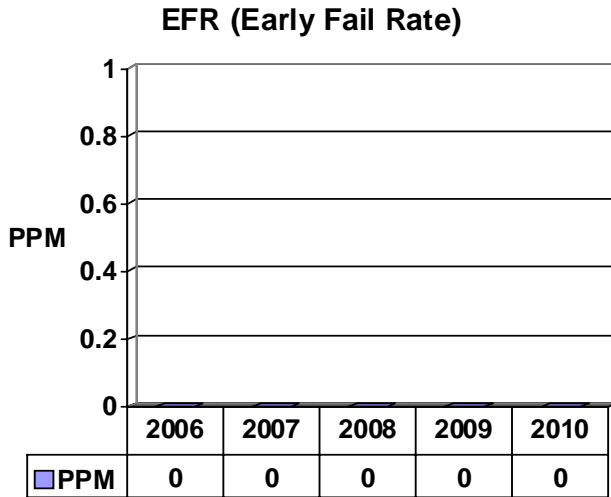
FIT: Failure in Time; 60% CL, 55°C, Ea = .7eV

IFR: Intrinsic Failure Rate > 168 hours @ the test temperature of 125°C or > 72 hours @ 150°C

IFR: Early Failure Rate < 168 hours @ the test temperature of 125°C or < 72 hours @ 150°C

Factory: Episil, Taiwan

Process: 1.2 μ / 2 μ CMOS



Year	Sample Size	# Fail	PPM
2006	616	0	0
2007	693	0	0
2008	319	0	0
2009	1290	0	0
2010	287	0	0

Year	Sample Size	Device Hours	# Fail
2006	616	616,000	0
2007	693	693,000	0
2008	319	559,000	0
2009	1290	1,290,000	0
2010	287	287,000	0

FIT: Failure in Time; 60% CL, 55°C, Ea = .7eV

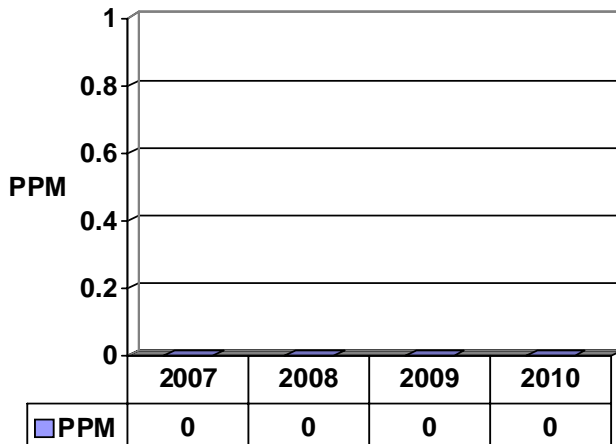
IFR: Intrinsic Failure Rate > 168 hours @ the test temperature of 125°C or > 72 hours @ 150°C

IFR: Early Failure Rate < 168 hours @ the test temperature of 125°C or < 72 hours @ 150°C

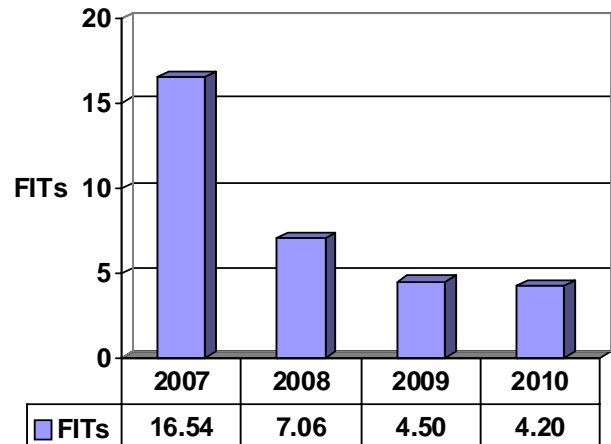
Factory: Silan, China

Process: 2 μ CMOS

EFR (Early Fail Rate)



IFR (Intrinsic Fail Rate)



Year	Sample Size	# Fail	PPM
2007	711	0	0
2008	953	0	0
2009	946	0	0
2010	157	0	0

Year	Sample Size	Device Hours	# Fail
2007	711	711,000	0
2008	953	953,000	0
2009	946	946,000	0
2010	157	157,000	0

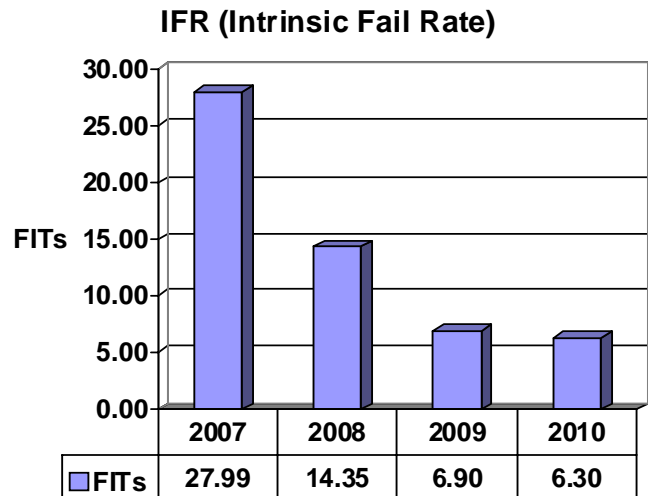
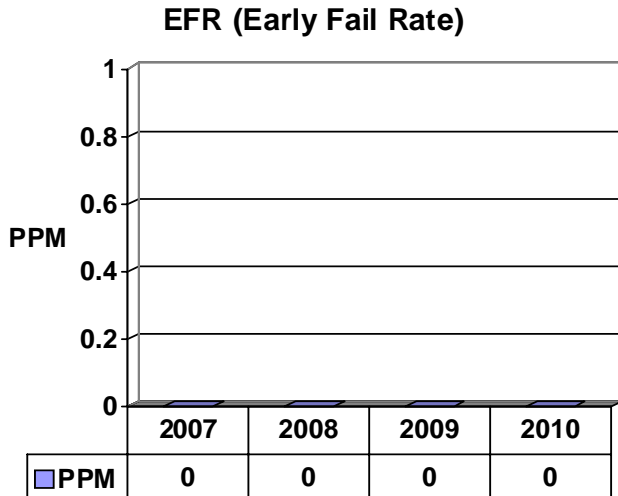
FIT: Failure in Time; 60% CL, 55°C, Ea = .7eV

IFR: Intrinsic Failure Rate > 168 hours @ the test temperature of 125°C or > 72 hours @ 150°C

IFR: Early Failure Rate < 168 hours @ the test temperature of 125°C or < 72 hours @ 150°C

Factory: Silan, China

Process: 5 μ CMOS



Year	Sample Size	# Fail	PPM
2007	420	0	0
2008	399	0	0
2009	893	0	0
2010	160	0	0

Year	Sample Size	Device Hours	# Fail
2007	420	420,000	0
2008	399	399,000	0
2009	893	893,000	0
2010	160	160,000	0

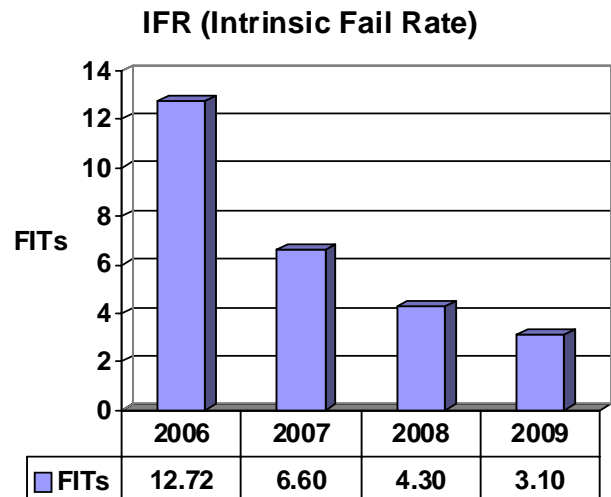
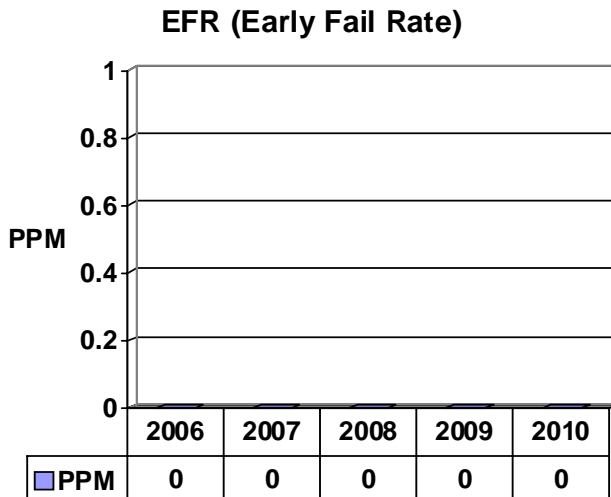
FIT: Failure in Time; 60% CL, 55°C, Ea = .7eV

IFR: Intrinsic Failure Rate > 168 hours @ the test temperature of 125°C or > 72 hours @ 150°C

IFR: Early Failure Rate < 168 hours @ the test temperature of 125°C or < 72 hours @ 150°C

Factory: Silan, China

Process: Bipolar



Year	Sample Size	# Fail	PPM
2006	1,600	0	0
2007	856	0	0
2008	721	0	0
2009	989	0	0
2010	320	0	0

Year	Sample Size	Device Hours	# Fail
2006	924	924,000	0
2007	858	856,000	0
2008	721	721,000	0
2009	989	604,000	0
2010	320	320,000	0

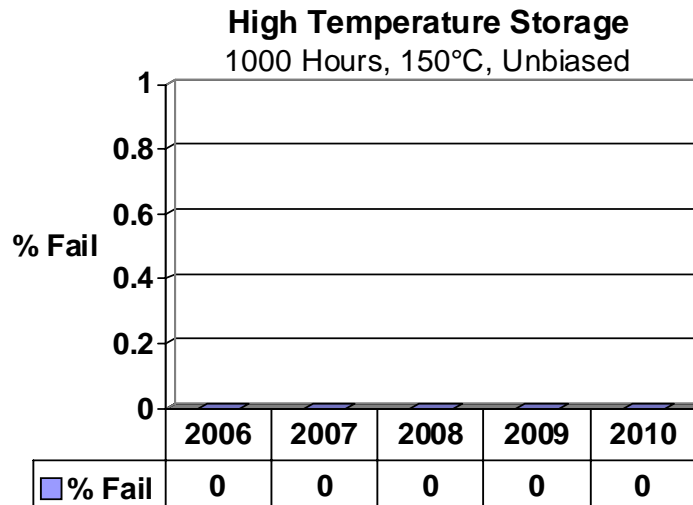
FIT: Failure in Time; 60% CL, 55°C, Ea = .7eV

IFR: Intrinsic Failure Rate > 168 hours @ the test temperature of 125°C or > 72 hours @ 150°C

IFR: Early Failure Rate < 168 hours @ the test temperature of 125°C or < 72 hours @ 150°C

Factory: GLOBALFOUNDRIES, Singapore

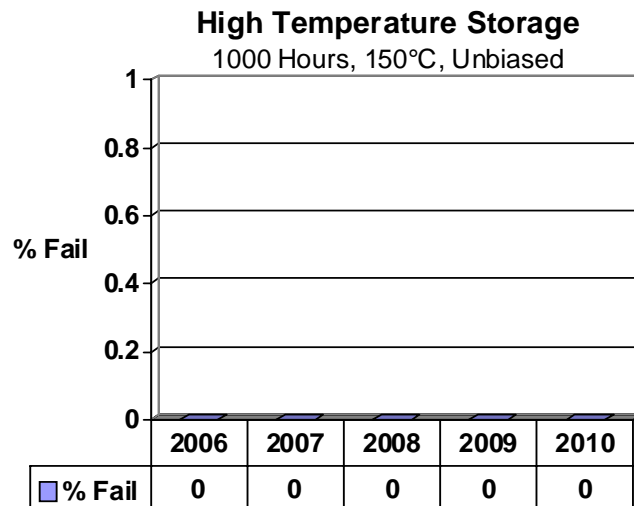
Process: 0.35 μ CMOS



Year	Sample Size	# Fail	% Fail
2006	322	0	0
2007	157	0	0
2008	75	0	0
2009	170	0	0
2010	65	0	0

Factory: GLOBALFOUNDRIES, Singapore

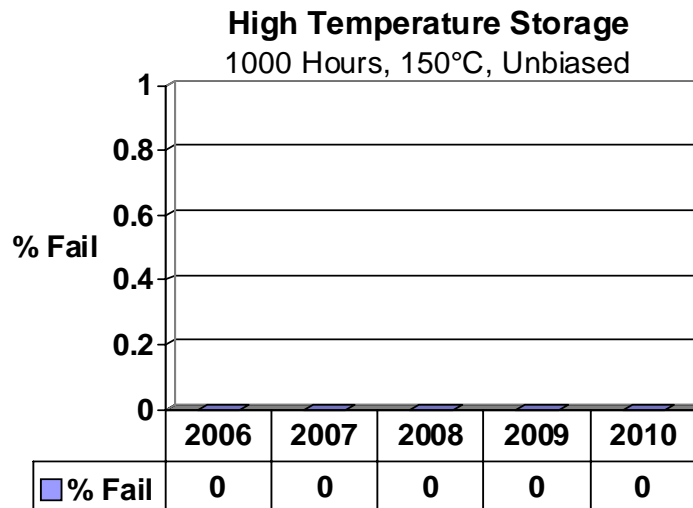
Process: 0.18 μ CMOS



Year	Sample Size	# Fail	% Fail
2006	75	0	0
2007	83	0	0
2008	45	0	0
2009	65	0	0
2010	120	0	0

Factory: GLOBALFOUNDRIES, Fab 2, Singapore

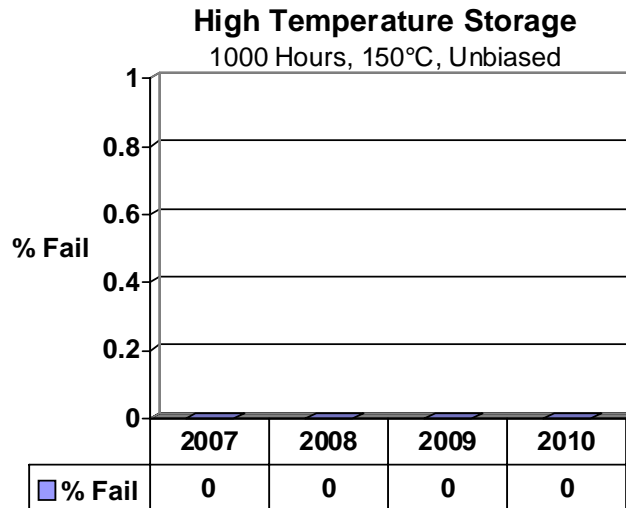
Process: 0.6 μ CMOS



Year	Sample Size	# Fail	% Fail
2005	180	0	0
2006	579	0	0
2007	135	0	0
2008	100	0	0
2009	180	0	0
2010	45	0	0

Factory: Tower/Jazz, CA USA

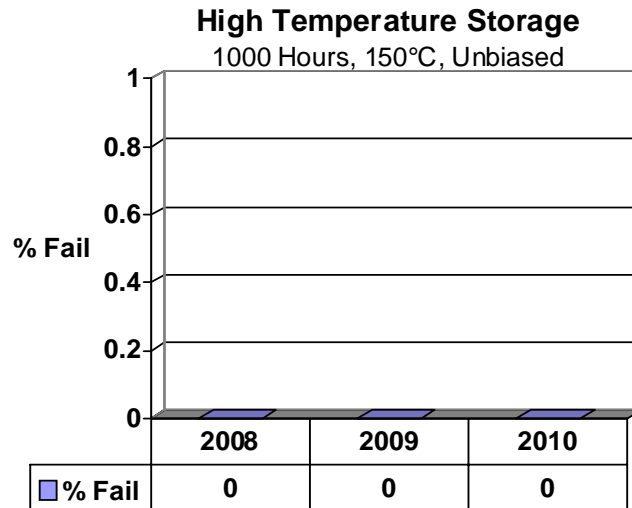
Process: 0.5 μ CMOS



Year	Sample Size	# Fail	% Fail
2007	231	0	0
2008	25	0	0
2009	282	0	0
2010	126	0	0

Factory: Episil, Taiwan

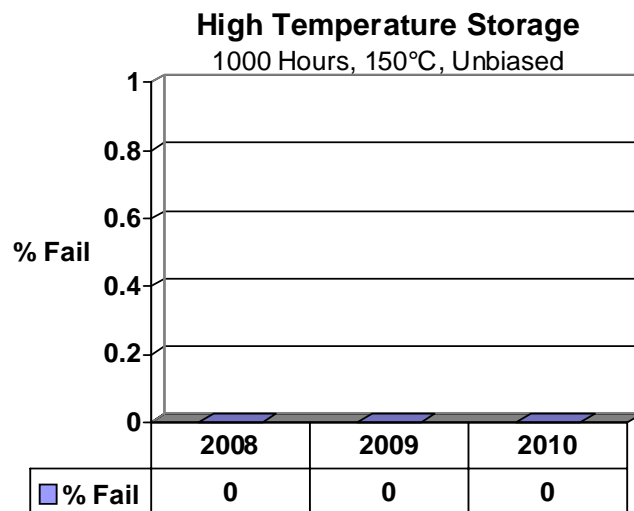
Process: 1.2 μ CMOS



Year	Sample Size	# Fail	% Fail
2008	80	0	0
2009	225	0	0
2010	70	0	0

Factory: Episil, Taiwan

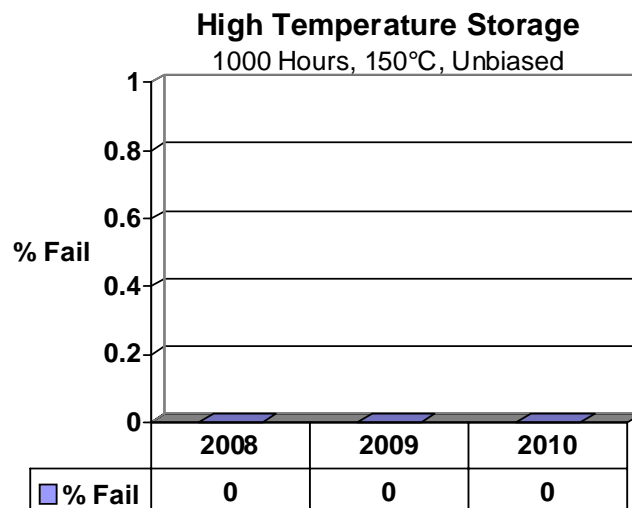
Process: 2 μ CMOS



Year	Sample Size	# Fail	% Fail
2008	462	0	0
2009	137	0	0
2010	154	0	0

Factory: Silan, China

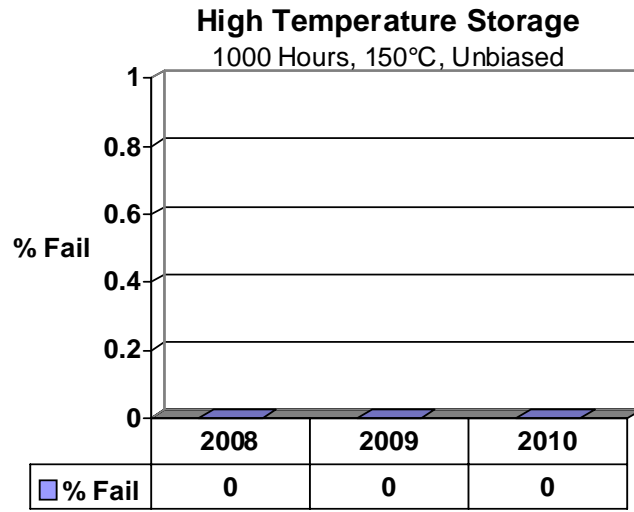
Process: 2 μ CMOS



Year	Sample Size	# Fail	% Fail
2008	204	0	0
2009	878	0	0
2010	110	0	0

Factory: Silan, China

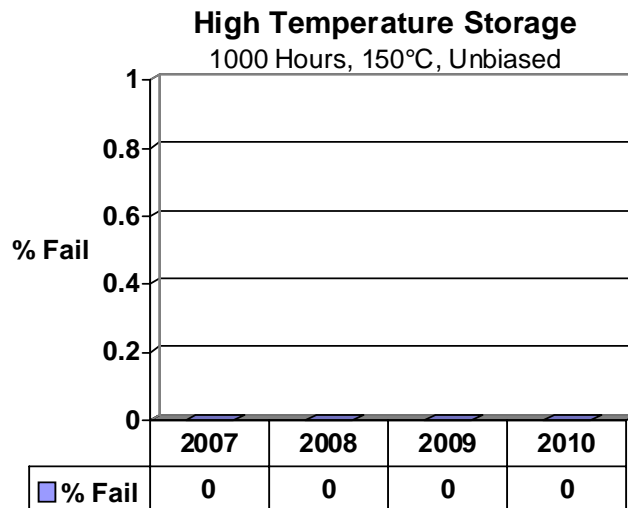
Process: 5 μ CMOS



Year	Sample Size	# Fail	% Fail
2008	77	0	0
2009	185	0	0
2010	157	0	0

Factory: Silan, China

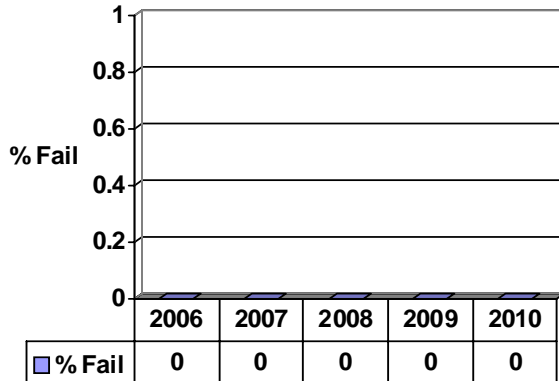
Process: Bipolar



Year	Sample Size	# Fail	% Fail
2007	180	0	0
2008	116	0	0
2009	347	0	0
2010	205	0	0

Package: BGA Families

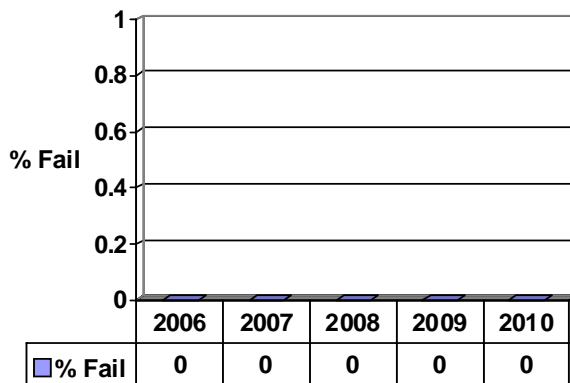
Temperature Cycle



Year	Sample Size	# Fail	% Fail
2006	256	0	0
2007	127	0	0
2008	47	0	0
2009	74	0	0
2010	176	0	0

Conditions:
1000 Cycles -55/125°C

Pressure Pot/UHAST

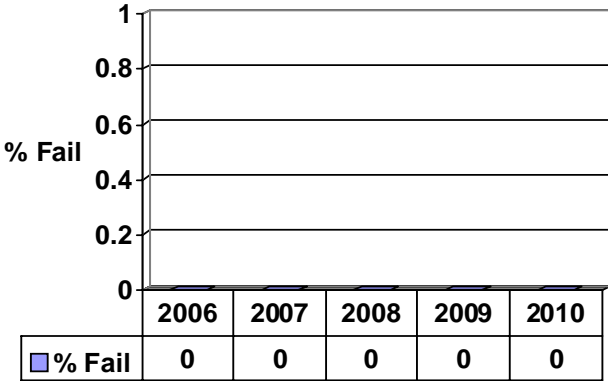


Year	Sample Size	# Fail	% Fail
2006	212	0	0
2007	97	0	0
2008	68	0	0
2009	74	0	0
2010	176	0	0

Conditions:
96 Hours, 130°C, 85% RH

Package: PDIP

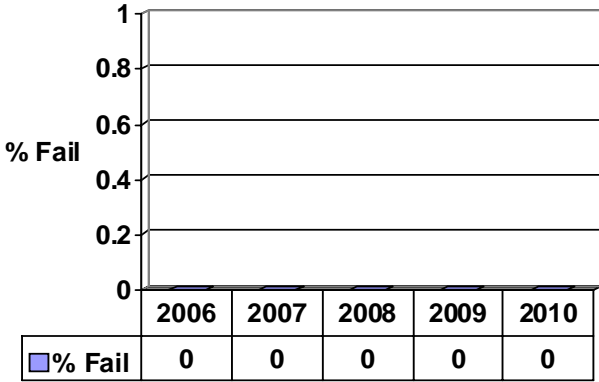
Temperature Cycle



Year	Sample Size	# Fail	% Fail
2006	90	0	0
2007	243	0	0
2008	135	0	0
2009	225	0	0
2010	102	0	0

Conditions:
1000 Cycles -65/150°C

Pressure Pot/UHAST

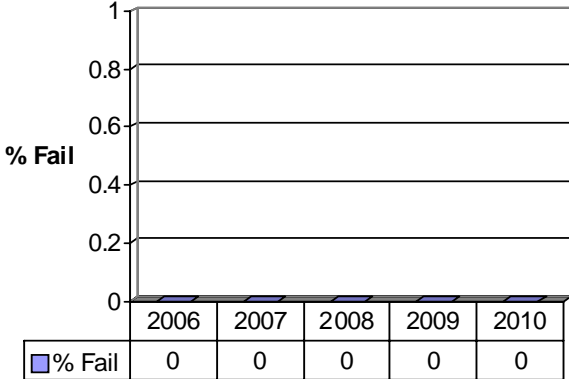


Year	Sample Size	# Fail	% Fail
2005	540	0	0
2006	225	0	0
2007	353	0	0
2008	135	0	0
2009	225	0	0
2010	102	0	0

Conditions:
96/168 Hours, 121°C, 100% RH / or 96 Hours, 130°C, 85% RH

Package: PLCC

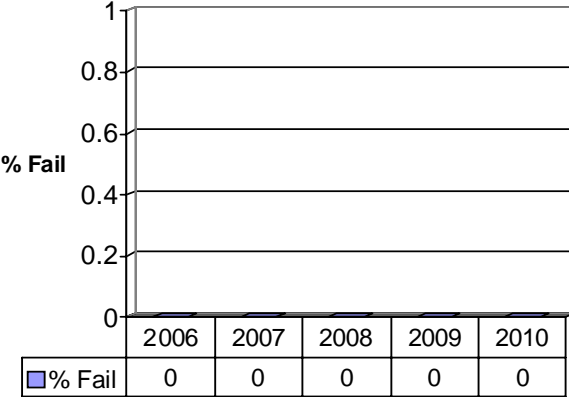
Temperature Cycle



Year	Sample Size	# Fail	% Fail
2006	135	0	0
2007	45	0	0
2008	90	0	0
2009	45	0	0
2010	135	0	0

Conditions:
1000 Cycles -65/150°C

Pressure Pot/UHAST

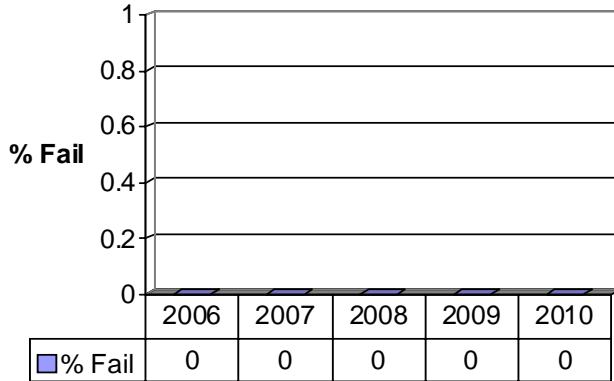


Year	Sample Size	# Fail	% Fail
2006	360	0	0
2007	90	0	0
2008	180	0	0
2009	45	0	0
2010	135	0	0

Conditions:
96 Hours, 130°C, 85% RH

Package: T/S/LQFP

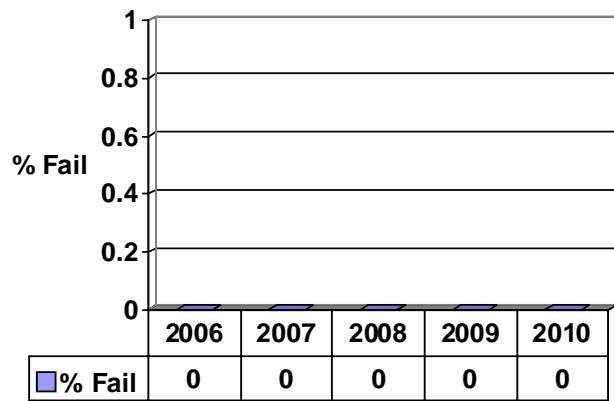
Temperature Cycle



Year	Sample Size	# Fail	% Fail
2006	724	0	0
2007	645	0	0
2008	180	0	0
2009	310	0	0
2010	180	0	0

Conditions:
300/1000 Cycles -65/150°C

Pressure Pot/UHAST

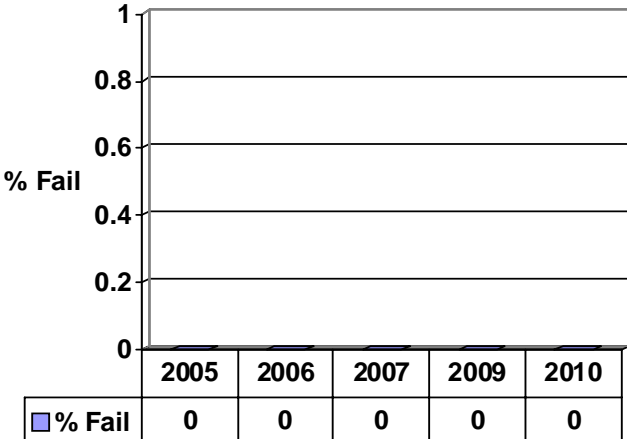


Year	Sample Size	# Fail	% Fail
2006	820	0	0
2007	460	0	0
2008	225	0	0
2009	321	0	0
2010	180	0	0

Conditions:
96 Hours, 130°C, 85% RH

Package: TO

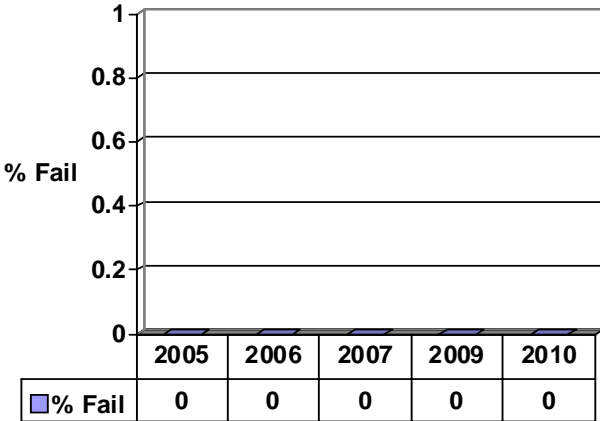
Temperature Cycle



Year	Sample Size	# Fail	% Fail
2005	500	0	0
2006	180	0	0
2007	180	0	0
2009	855	0	0
2010	424	0	0

Conditions:
1000Cycles, -65/150°C

Pressure Pot/UHAST

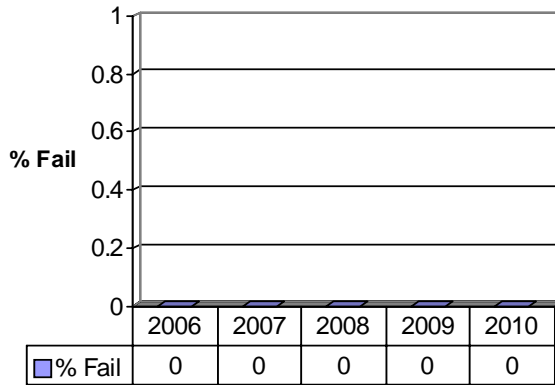


Year	Sample Size	# Fail	% Fail
2005	855	0	0
2006	310	0	0
2007	313	0	0
2009	855	0	0
2010	469	0	0

Conditions:
96 Hours, 130°C, 85% RH

Package: SOT, TSOT, SC-70

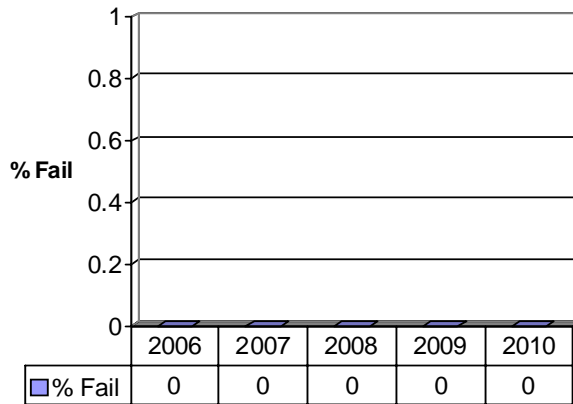
Temperature Cycle



Year	Sample Size	# Fail	% Fail
2006	77	0	0
2007	908	0	0
2008	1780	0	0
2009	1042	0	0
2010	771	0	0

Conditions:
500/1000 Cycles -65/150°C

Pressure Pot/UHAST

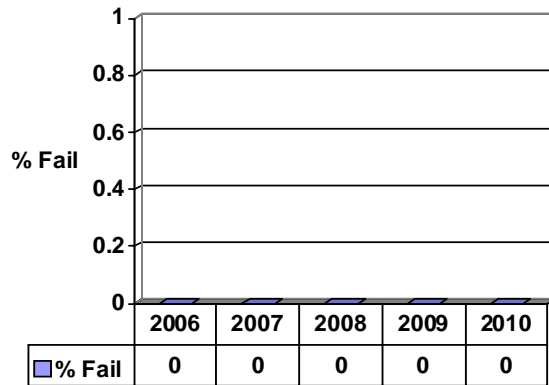


Year	Sample Size	# Fail	% Fail
2006	77	0	0
2007	915	0	0
2008	836	0	0
2009	1042	0	0
2010	771	0	0

Conditions:
96 Hours, 121°C, 100% RH / or 96 Hours, 130°C, 85% RH

Package: MSOP, TSSOP, SSOP, SOIC

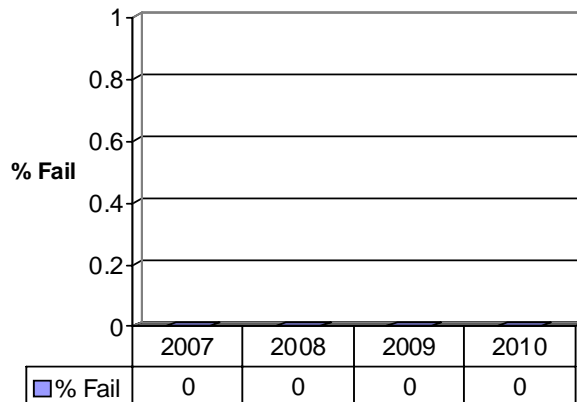
Temperature Cycle



Year	Sample Size	# Fail	% Fail
2006	539	0	0
2007	2731	0	0
2008	2538	0	0
2009	3058	0	0
2010	1015	0	0

Conditions:
300/1000Cycles, -65/150°C

Pressure Pot/UHAST

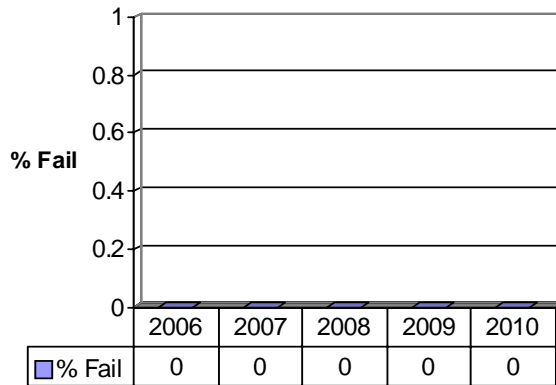


Year	Sample Size	# Fail	% Fail
2007	1131	0	0
2008	2253	0	0
2009	3189	0	0
2010	1134	0	0

Conditions:
96 Hours, 121°C, 100% RH / or 96 Hours, 130°C, 85% RH

Package: DFN/QFN

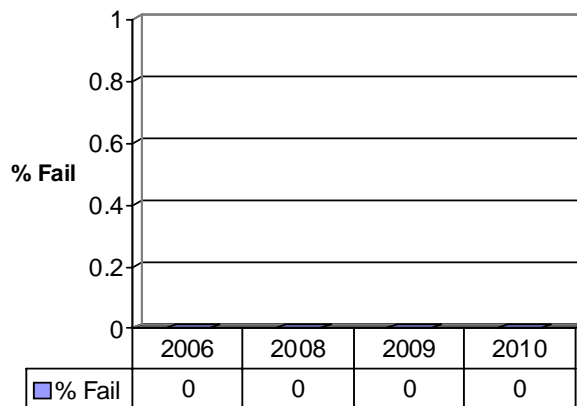
Temperature Cycle



Year	Sample Size	# Fail	% Fail
2006	231	0	0
2007	77	0	0
2008	45	0	0
2009	85	0	0
2010	70	0	0

Conditions:
1000 Cycles -65/150°C,

Pressure Pot/UHAST



Year	Sample Size	# Fail	% Fail
2006	308	0	0
2008	25	0	0
2009	220	0	0
2010	70	0	0

Conditions:
96 Hours, 121°C, 100% RH / or 96 Hours,
130°C, 85% RH